

400V High Voltage NPN Transistor

FEATURES

- Epitaxial Planar Type
- NPN Silicon Transistor
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

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- Consumer electronics
- High voltage switching
- High voltage driver

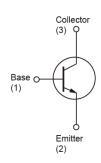
KEY PERFORMANCE PARAMETERS				
F	PARAMETER	VALUE	UNIT	
BV_CBO		400	V	
	BV_CEO	400	V	
	I _C	300	mA	
V _{CE(SAT)}	I _C =10mA, I _B =1mA	0.1	V	











Notes: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Collector-Base Voltage	V_{CBO}	400	V		
Collector-Emitter Voltage	V_{CEO}	400	V		
Emitter-Base Voltage	V_{EBO}	6	V		
Collector Current (DC)	I _C	300	mA		
Power Total Dissipation @ T _A =25°C	P _D	0.225	W		
Maximum Operating Junction Temperature	T _J	+150	°C		
Storage Temperature Range	T _{STG}	-55 to +150	°C		

Note: Single pulse, $Pw \le 380\mu s$, $Duty \le 2\%$

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	TYP	UNIT	
Junction to Ambient Thermal Resistance	$R_{\Theta JA}$	556	°C/W	
Junction to Case Thermal Resistance	R _{eJC}	185	°C/W	





ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 1)						
Collector-Base Breakdown Voltage	I _C =50uA, I _E =0	BV _{CBO}	400			V
Collector-Emitter Breakdown Voltage	$I_C = 1 \text{mA}, I_B = 0$	BV _{CEO}	400			V
Emitter-Base Breakdown Voltage	I _E =50uA, I _C =0	BV _{EBO}	6			V
Collector Cutoff Current	V _{CB} =400V, I _E =0	I _{CBO}			10	μA
Collector-Emitter Reverse Current	$V_{CE} = 300V, R_{EB} = 4k\Omega$	I _{CER}			20	nA
Emitter Cutoff Current	$V_{EB} = 6V, I_{C} = 0$	I _{EBO}			10	μA
Collector-Emitter Saturation Voltage	$I_C = 10mA$, $I_B = 1mA$	V _{CE(SAT)}		0.1	0.5	V
Base-Emitter Saturation Voltage	$I_C = 10mA$, $I_B = 1mA$	V _{BE(SAT)}			1.5	V
DC Current Transfer Ratio	$V_{CE} = 10V$, $I_{C} = 10mA$	h _{FE}	100		270	
Dynamic (Note 2)						
Transition Frequency	V_{CE} =10V, I_{C} =-10mA, f =10MHz	f _T		20		MHz
Output Capacitance	V _{CB} =10V, I _E =0, f=1MHz	C _{ob}		7		pF

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Note:

- 1. Pulse test: ≤380µs, duty cycle ≤2%
- 2. For DESIGN AID ONLY, not subject to production testing

ORDERING INFORMATION

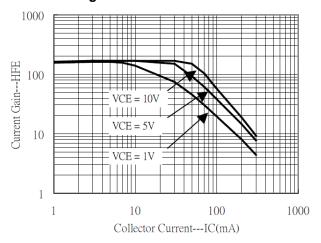
ORDERING CODE	PACKAGE	PACKING
TSC4505CX RFG	SOT-23	3,000pcs / 7" Reel

100



ELECTRICAL CHARACTERICS CURVES ($T_A=25^{\circ}C$, unless otherwise noted)

Figure 1. DC Current Gain



Saturation Voltage---(mV) 100 VCE(SAT) @ IC = 10IB

10000

1000

10

Figure 3. V_{BE(SAT)} v.s. Ic

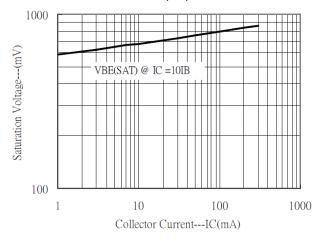


Figure 4. Power Derating Curve

10

Collector Current---IC(mA)

Figure 2. V_{CE(SAT)} v.s. Ic

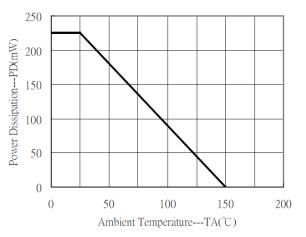
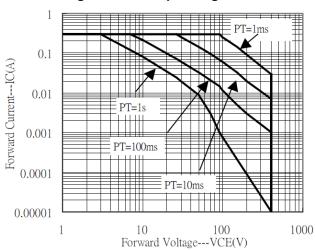


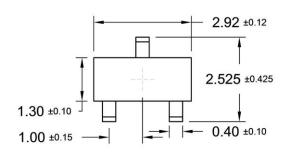
Figure 5. Safe Operating Area

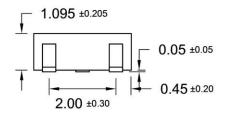


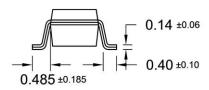


PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

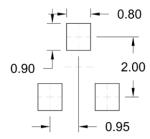
SOT-23







SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



3D = Device Code

x = Year Code

7=2017, 8=2018, 9=2019, 0=2020.......

x = Month Code

1 =Jan

2 =Feb

3 =Mar

4 =Apr

5 =May

6 =Jun

7 =Jul

8 =Aug

9 =Sep

A =Oct

B =Nov

C =Dec



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